

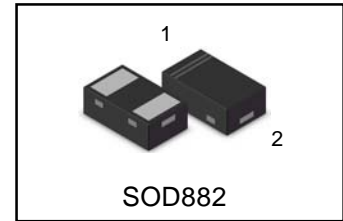
LBAS40BST5G

S-LBAS40BST5G

Schottky barrier diode

1. FEATURES

- Low forward current
- Guard ring protected
- Low diode capacitance.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



2. APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits.
- Blocking diodes.

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAS40BST1G	B1	5000/Tape&Reel
LBAS40BST3G	B1	8000/Tape&Reel
LBAS40BST5G	B1	10000/Tape&Reel

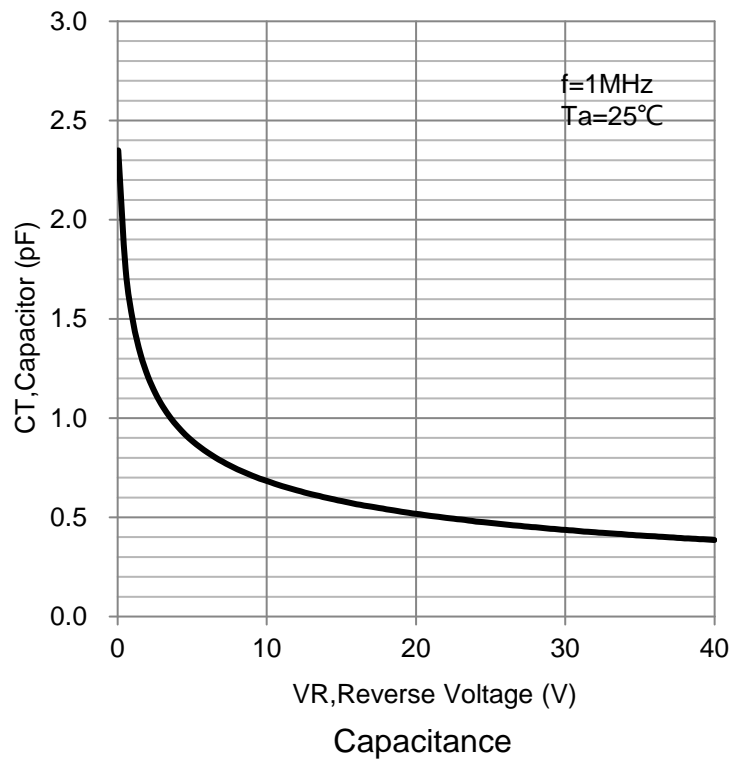
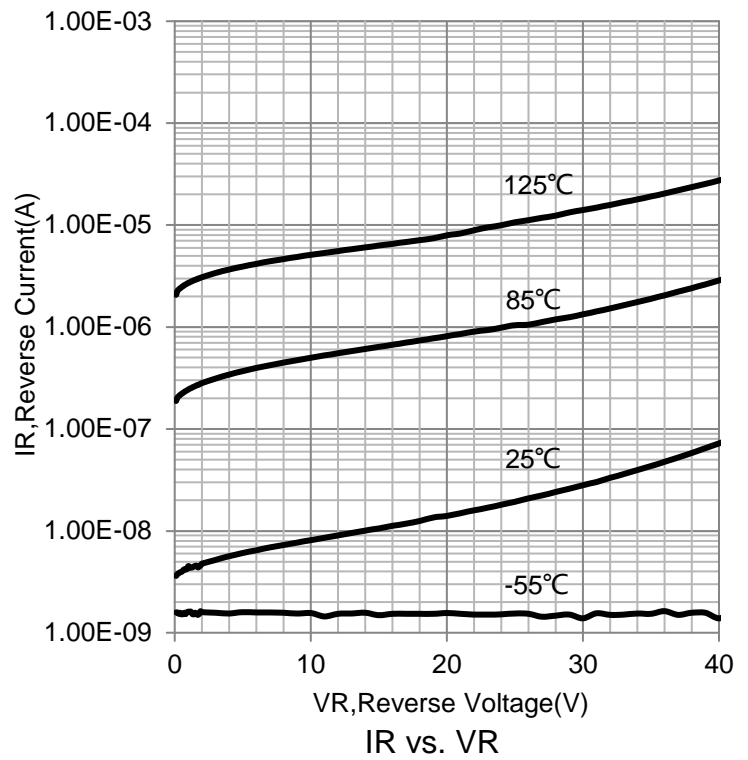
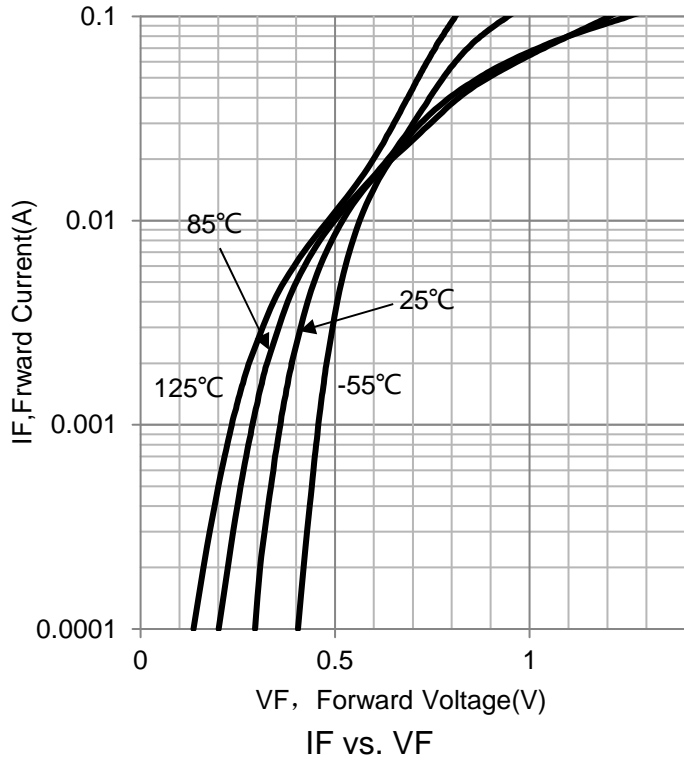
4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Continuous reverse voltage	VR	40	V
Continuous forward current	IF	120	mA
Repetitive Peak forward surge current	IFSM	120	mA
Non-repetitive peak forward current	IFSM	200	mA
Storage temperature	TSTG	-65~+125	°C
Junction temperature	Tj	125	°C
Operating ambient temperature	Tamb	-65~+125	°C
Typical thermal resistance (FR-4 mini PAD)	RθJA	833	K/W

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

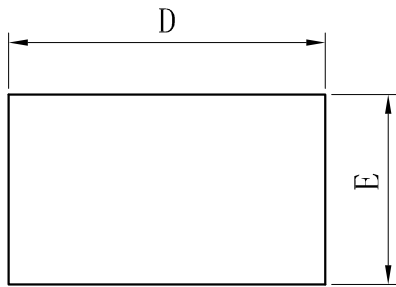
Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	IF =1mA	VF1	-	400	mV
	IF =10mA	VF2	-	560	mV
	IF =40mA	VF3	-	1	V
Reverse current	VR=1.8V	IR	-	10	nA
	VR=30V		-	0.2	μA
	VR=40V		-	10	μA
Capacitance	VR=0V,f=1MHz	Cd	-	5	pF

6.ELECTRICAL CHARACTERISTICS CURVES

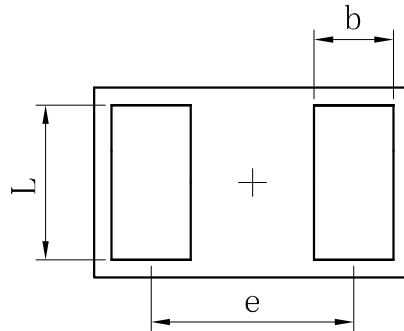


7.OUTLINE AND DIMENSIONS

SOD882

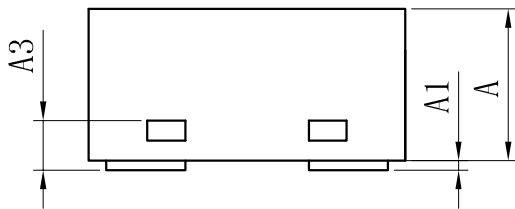


TOP VIEW



BOTTOM VIEW

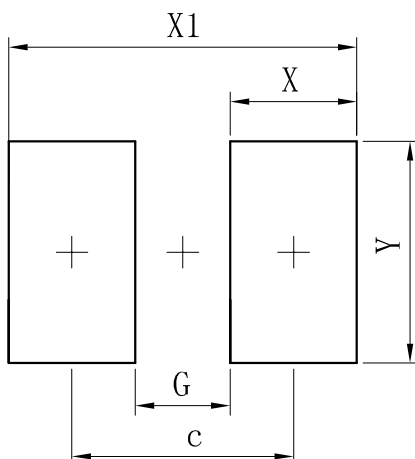
SOD882			
Dim	Min	Typ	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	-	0.05
A3	0.127REF.		
All Dimensions in mm			



SIDE VIEW

8.SOLDERING FOOTPRINT

SOD882



Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)